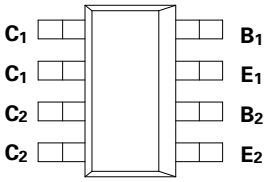
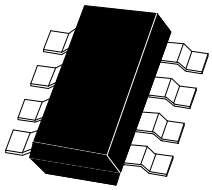
SM-8 DUAL PNP MEDIUM POWER TRANSISTORS

ISSUE 1 - AUGUST 1997

ZDT751



PARTMARKING DETAIL – T751



SM-8
(8 LEAD SOT223)

ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	-80	V
Collector-Emitter Voltage	V_{CEO}	-60	V
Emitter-Base Voltage	V_{EBO}	-5	V
Peak Pulse Current	I_{CM}	-6	A
Continuous Collector Current	I_C	-2	A
Operating and Storage Temperature Range	T_j:T_{stg}	-55 to +150	°C

THERMAL CHARACTERISTICS

PARAMETER	SYMBOL	VALUE	UNIT
Total Power Dissipation at T_{amb} = 25°C* Any single die "on" Both die "on" equally	P_{tot}	 2.25 2.75	 W W
Derate above 25°C* Any single die "on" Both die "on" equally		 18 22	 mW/ °C mW/ °C
Thermal Resistance - Junction to Ambient* Any single die "on" Both die "on" equally		 55.6 45.5	 °C/ W °C/ W

* The power which can be dissipated assuming the device is mounted in a typical manner on a PCB with copper equal to 2 inches square.

Zetex plc.
Fields New Road, Chadderton, Oldham, OL9-8NP, United Kingdom.
Telephone: (44)161-627 5105 (Sales), (44)161-627 4963 (General Enquiries)
Fax: (44)161-627 5467

Zetex GmbH
Streitfeldstraße 19
D-81673 München
Germany
Telefon: (49) 89 45 49 49 0
Fax: (49) 89 45 49 49 49

Zetex Inc.
47 Mall Drive, Unit 4
Commack NY 11725
USA
Telephone: (516) 543-7100
Fax: (516) 864-7630

Zetex (Asia) Ltd.
3510 Metroplaza, Tower 2
Hing Fong Road,
Kwai Fong, Hong Kong
Telephone:(852) 26100 611
Fax: (852) 24250 494

These are supported by agents and distributors in major countries world-wide

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Internet:
http://www.zetex.com

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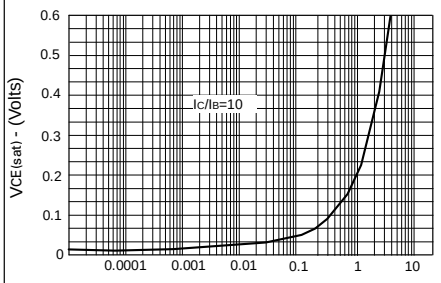
ELECTRICAL CHARACTERISTICS (at T_{amb} = 25°C unless otherwise stated).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-80			V	I_C=-100μA, I_E=0
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-60			V	I_C=-10mA, I_B=0*
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5			V	I_E=-100μA, I_C=0
Collector Cutoff Current	I_{CBO}			-0.1 -10	μA μA	V_{CB}=-60V V_{CB}=-60V,T_{amb}=100°C
Emitter Cutoff Current	I_{EBO}			-0.1	μA	V_{EB}=-4V, I_E=0
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		-0.15 -0.28	-0.3 -0.5	V V	I_C=1A, I_B=-100mA* I_C=2A, I_B=-200mA*
Base-Emitter Saturation Voltage	$V_{BE(sat)}$		-0.9	-1.25	V	I_C=1A, I_B=-100mA*
Base-Emitter Turn-On Voltage	$V_{BE(on)}$		-0.8	-1	V	I_C=-1A, V_{CE}=-2V*
Static Forward Current Transfer Ratio	h_{FE}	70 100 80 40	200 200 170 80	300		I_C=-50mA, V_{CE}=-2V* I_C=-500mA, V_{CE}=-2V* I_C=-1A, V_{CE}=-2V* I_C=-2A, V_{CE}=-2V*
Transition Frequency	f_T	100	140		MHz	I_C=-100mA, V_{CE}=-5V f=100MHz
Output Capacitance	C_{obo}			30	pF	V_{CB}=-10V f=1MHz
Switching Times	t_{on}		40		ns	I_C=-500mA, V_{CC}=-10V I_{B1}=I_{B2}=-50mA
	t_{off}		450		ns	

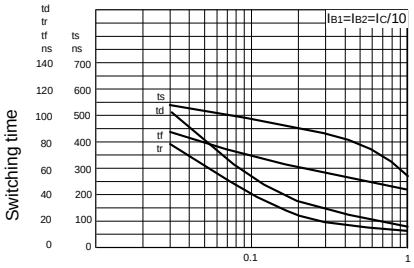
*Measured under pulsed conditions. Pulse width=300μs. Duty cycle ≤ 2%

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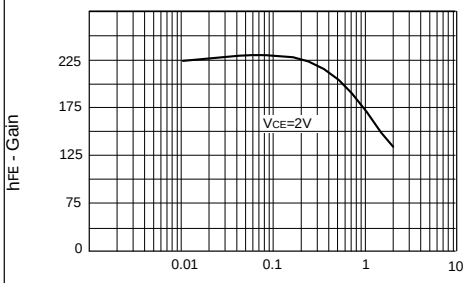
TYPICAL CHARACTERISTICS



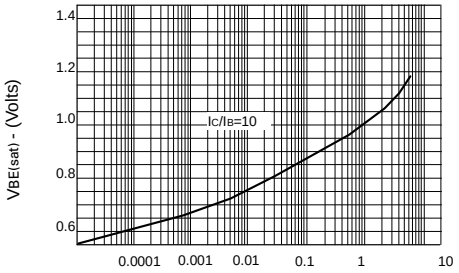
VCE(sat) v IC



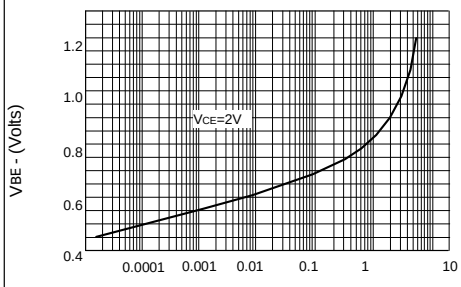
Switching Speeds



hFE v IC



VBE(sat) v IC



VBE(on) v IC